

ABSTRACT

An MIS transistor having a T shaped gate is characterised by the presence of a shaping material (14) 5 coating a T shaped solid form. The gate structure is lodged in the envelope formed by the shaping material (14). The coating of the T shape of the gate by the shaping material (14) is carried out at the very start of forming the gate structure and is chosen in such a way that it withstands all subsequent 10 manufacturing treatments of the transistor and subsists, thus defining the definitive shape of the gate structure. One thus obtains a perfectly controlled gate shape.

Figure 12

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